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Fabrication of transparent conducting films composed of In^{3+} doped CuS and their application in flexible electroluminescent devices

Dinesh K. Patel[a], Alexander Kamyshny[a], Ariando[b], Huang Zhen[b], and Shlomo Magdassi[a,]*

[a]Casali Center for Applied Chemistry, Institute of Chemistry, The Center for Nanoscience and Nanotechnology, The Hebrew University of Jerusalem, Jerusalem 9190401, Israel.

[b]NUSNNI-Nanocore & Department of Physics, National University of Singapore, 117411 Singapore.

E-mail: magdassi@mail.huji.ac.il

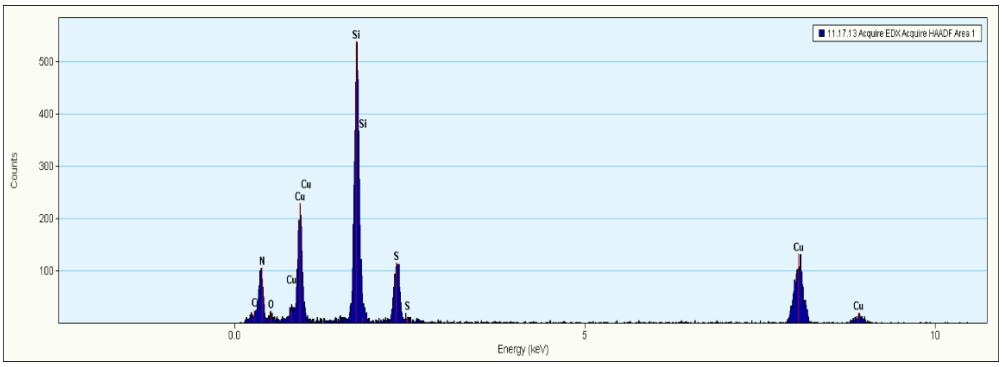

Fig. S1 EDS pattern of undoped CuS on silicon grid coated with silicon nitride.

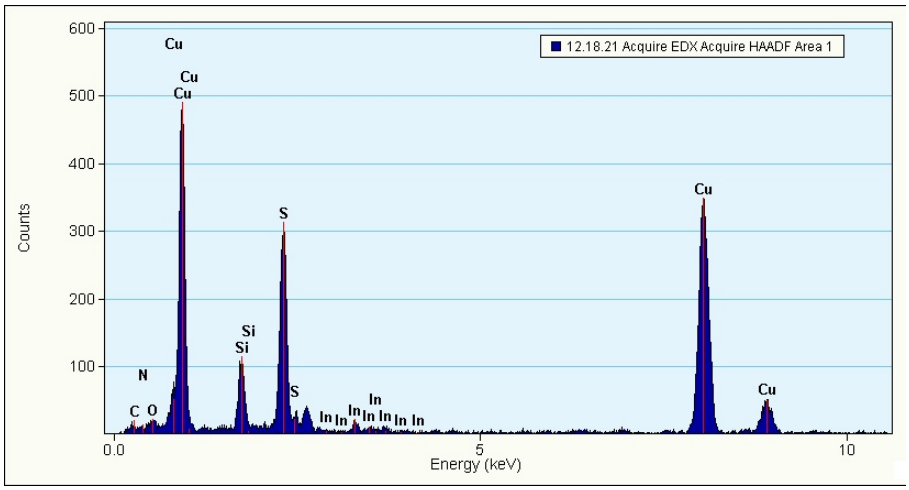

Fig. S2 EDS of CuS films doped with 2.5 mol. % In^{3+} ions on silicon grid coated with silicon nitride.

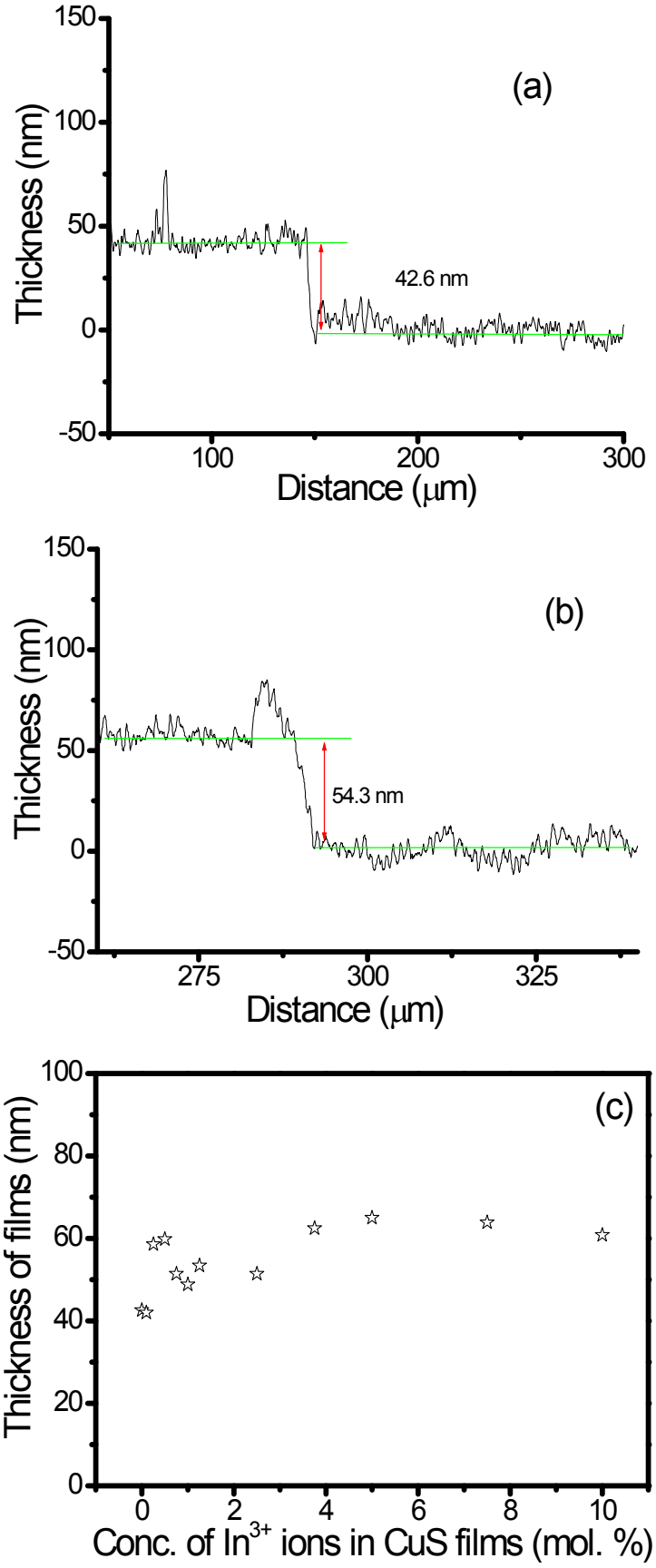

Fig. S3 Profiles of CuS films doped with (a) 0 and (b) 1% In^{3+} ions (c) thickness of the films with varying concentration of In^{3+} ions with dipping time 24 hours.